

XP-002167343

AN - 1997-347912 [32]

AP - JP19950331110 19951127

CPY - HITK

DC - M13 P55

FS - CPI;GMPI

IC - B23K20/00 ; C23C14/34

MC - M13-G02

PA - (HITK) HITACHI METALS LTD

PN - JP9143704 A 19970603 DW199732 C23C14/34 001pp

PR - JP19950331110 19951127

XA - C1997-112372

XIC - B23K-020/00 ; C23C-014/34

XP - N1997-288352

AB - J09143704 The Ti-target is made by isostatic pressing Ti-target material and backing plate mainly of Al in contact state at 300-450 deg. C with a pressure of 50-200 MPa, to obtain a target material which is cemented by diffusing the target material having recrystallised structure of maximum grain size of up to 20 μ m. and mean crystal grain size of up to 10 μ m. and the backing plate.

- USE - For forming thin film contg. Ti by sputtering.

- (Dwg.0/2)

IW - TITANIUM TARGET MANUFACTURE SPUTTER ISOSTATIC PRESS TITANIUM TARGET MATERIAL BACKING PLATE ALUMINIUM SPECIFIC PRESSURE

IKW - TITANIUM TARGET MANUFACTURE SPUTTER ISOSTATIC PRESS TITANIUM TARGET MATERIAL BACKING PLATE ALUMINIUM SPECIFIC PRESSURE

NC - 001

OPD - 1995-11-27

ORD - 1997-06-03

PAW - (HITK) HITACHI METALS LTD

TI - Titanium target manufacture for sputtering - by isostatic pressing titanium target material and backing plate of aluminium at specific pressure etc